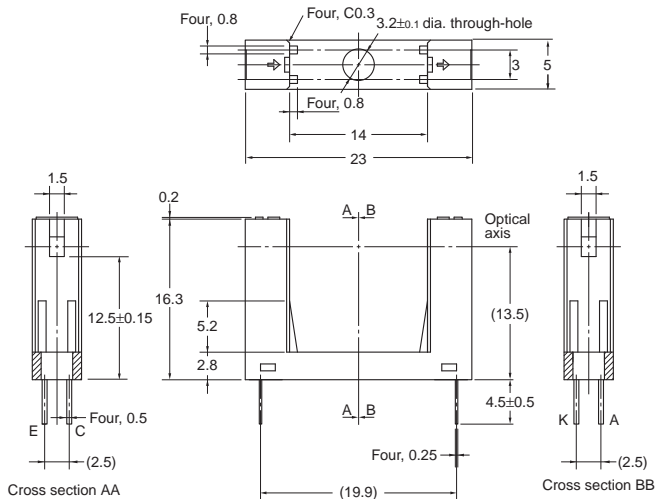


## Photomicrosensor (Transmissive) EE-SX1140

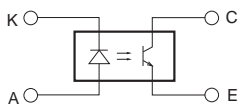
**⚠ Be sure to read *Precautions* on page 24.**

### ■ Dimensions

**Note:** All units are in millimeters unless otherwise indicated.



#### Internal Circuit



Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.3
3 < mm ≤ 6	±0.375
6 < mm ≤ 10	±0.45
10 < mm ≤ 18	±0.55
18 < mm ≤ 30	±0.65

Terminal No.	Name
A	Anode
K	Cathode
C	Collector
E	Emitter

### ■ Features

- General-purpose model with a 14-mm-wide slot.
- 16.3-mm-tall model with a deep slot.
- PCB mounting type.

### ■ Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rated value
Emitter	Forward current	$I_F$ 50 mA (see note 1)
	Pulse forward current	$I_{FP}$ 1 A (see note 2)
	Reverse voltage	$V_R$ 4 V
Detector	Collector–Emitter voltage	$V_{CEO}$ 30 V
	Emitter–Collector voltage	$V_{ECO}$ ---
	Collector current	$I_C$ 20 mA
	Collector dissipation	$P_C$ 100 mW (see note 1)
Ambient temperature	Operating	$T_{opr}$ -25°C to 85°C
	Storage	$T_{stg}$ -30°C to 100°C
Soldering temperature	$T_{sol}$	260°C (see note 3)

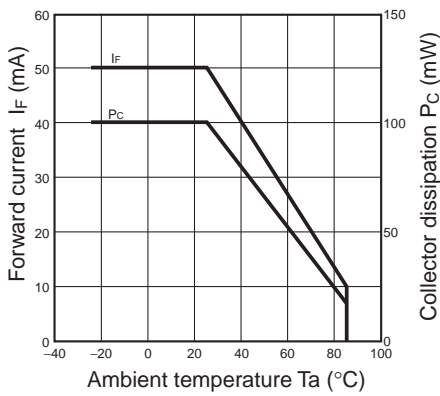
- Note:**
1. Refer to the temperature rating chart if the ambient temperature exceeds 25°C.
  2. The pulse width is 10  $\mu$ s maximum with a frequency of 100 Hz.
  3. Complete soldering within 10 seconds.

### ■ Electrical and Optical Characteristics (Ta = 25°C)

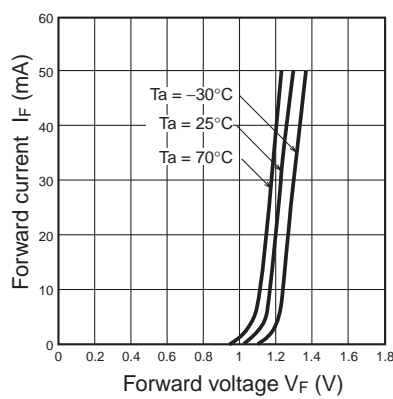
Item	Symbol	Value	Condition
Emitter	Forward voltage	$V_F$ 1.2 V typ., 1.5 V max.	$I_F = 30$ mA
	Reverse current	$I_R$ 0.01 $\mu$ A typ., 10 $\mu$ A max.	$V_R = 4$ V
	Peak emission wavelength	$\lambda_P$ 940 nm typ.	$I_F = 20$ mA
Detector	Light current	$I_L$ 0.4 mA min.	$I_F = 20$ mA, $V_{CE} = 10$ V
	Dark current	$I_D$ 2 nA typ., 200 nA max.	$V_{CE} = 10$ V, 0 lx
	Leakage current	$I_{LEAK}$ ---	---
	Collector–Emitter saturated voltage	$V_{CE(sat)}$ 0.1 V typ., 0.4 V max.	$I_F = 20$ mA, $I_L = 0.1$ mA
	Peak spectral sensitivity wavelength	$\lambda_P$ 850 nm typ.	$V_{CE} = 10$ V
Rising time	$t_r$	4 $\mu$ s typ.	$V_{CC} = 5$ V, $R_L = 100 \Omega$ , $I_L = 5$ mA
Falling time	$t_f$	4 $\mu$ s typ.	$V_{CC} = 5$ V, $R_L = 100 \Omega$ , $I_L = 5$ mA

■ Engineering Data

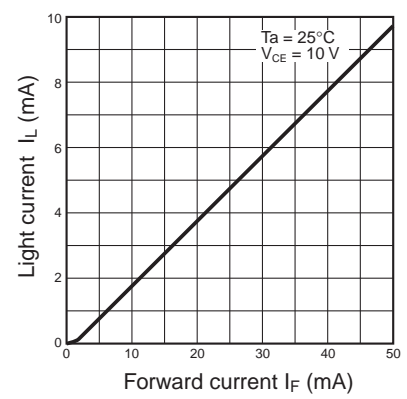
**Forward Current vs. Collector Dissipation Temperature Rating**



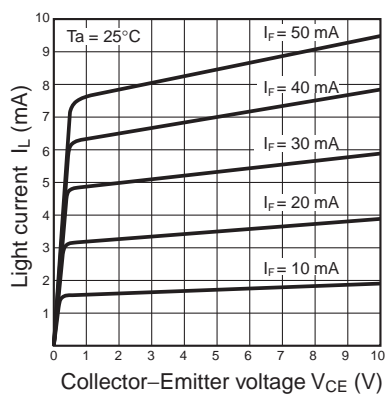
**Forward Current vs. Forward Voltage Characteristics (Typical)**



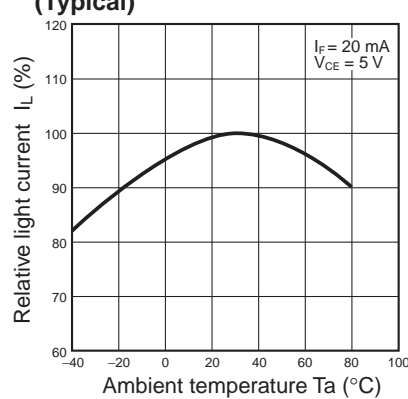
**Light Current vs. Forward Current Characteristics (Typical)**



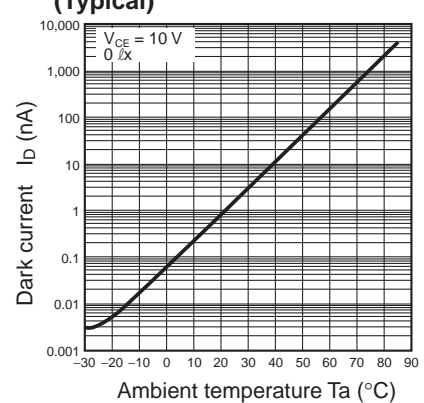
**Light Current vs. Collector-Emitter Voltage Characteristics (Typical)**



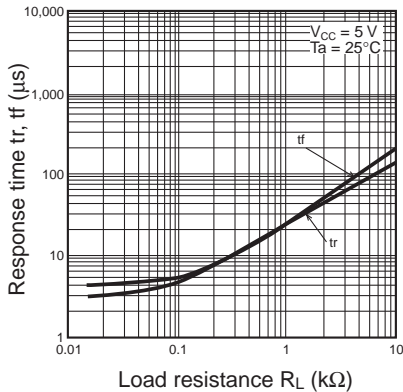
**Relative Light Current vs. Ambient Temperature Characteristics (Typical)**



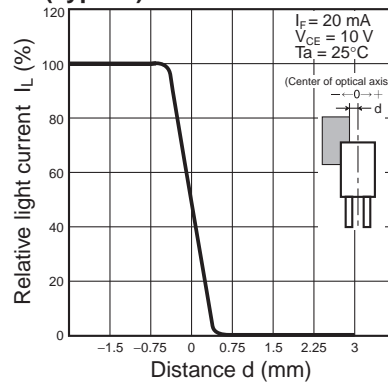
**Dark Current vs. Ambient Temperature Characteristics (Typical)**



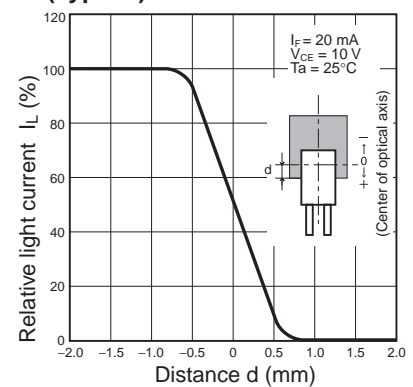
**Response Time vs. Load Resistance Characteristics (Typical)**



**Sensing Position Characteristics (Typical)**



**Sensing Position Characteristics (Typical)**



**Response Time Measurement Circuit**

